

FDZ203N

N-Channel 2.5V Specified PowerTrench® BGA MOSFET

General Description

Combining Fairchild's advanced 2.5V specified PowerTrench process with state of the art BGA packaging, the FDZ203N minimizes both PCB space and $R_{DS(ON)}$. This BGA MOSFET embodies a breakthrough in packaging technology which enables the device to combine excellent thermal transfer characteristics, high current handling capability, ultra-low profile packaging, low gate charge, and low $R_{DS(ON)}$.

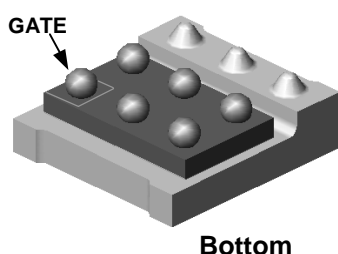
Applications

- Battery management
- Load switch
- Battery protection

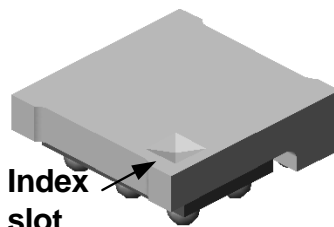


Features

- 7.5 A, 20 V. $R_{DS(ON)} = 18\text{ m}\Omega @ V_{GS} = 4.5$
 $R_{DS(ON)} = 30\text{ m}\Omega @ V_{GS} = 2.5\text{ V}$
- Occupies only 4 mm² of PCB area. Less than 40% of the area of a SSOT-6
- Ultra-thin package: less than 0.80 mm height when mounted to PCB
- Ultra-low $Q_g \times R_{DS(ON)}$ figure-of-merit.
- High power and current handling capability.
- RoHS Compliant

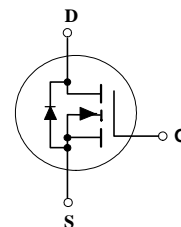


Bottom



Index slot

Top



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	Rated	Units
V _{DSS}	Drain-Source Voltage	20	V
V _{GSS}	Gate-Source Voltage	±12	V
I _D	Drain Current – Continuous (Note 1a)	7.5	A
		20	
P _D	Power Dissipation (Steady State) (Note 1a)	1.6	W
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

Symbol	Parameter	Rated	Units
R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1a)	67	°C/W
R _{θJB}	Thermal Resistance, Junction-to-Ball (Note 1)	11	
R _{θJC}	Thermal Resistance, Junction-to-Case (Note 1)	1	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
203N	FDZ203N	7"	8mm	3000 units

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		14		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 16\text{ V}, V_{GS} = 0\text{ V}$			1	μA
I_{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 12\text{ V}, V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -12\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	0.6	0.8	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		-3		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 4.5\text{ V}, I_D = 7.5\text{ A}$ $V_{GS} = 2.5\text{ V}, I_D = 5.5\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 7.5\text{ A}, T_J = 125^\circ\text{C}$		14 20	18 30 28	m Ω
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 4.5\text{ V}, V_{DS} = 5\text{ V}$	20			A
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 7.5\text{ A}$		33		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}$		1127		pF
C_{oss}	Output Capacitance	$f = 1.0\text{ MHz}$		268		pF
C_{riss}	Reverse Transfer Capacitance			134		pF

Switching Characteristics (Note 2)

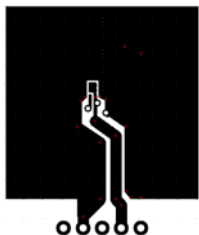
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 10\text{ V}, I_D = 1\text{ A}$		8	16	ns
t_r	Turn-On Rise Time	$V_{GS} = 4.5\text{ V}, R_{GEN} = 6\ \Omega$		11	20	ns
$t_{d(off)}$	Turn-Off Delay Time			26	42	ns
t_f	Turn-Off Fall Time			8	16	ns
Q_g	Total Gate Charge	$V_{DS} = 10\text{ V}, I_D = 7.5\text{ A}$		11	15	nC
Q_{gs}	Gate-Source Charge	$V_{GS} = 4.5\text{ V}$		2		nC
Q_{gd}	Gate-Drain Charge			3		nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current				1.3	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 1.3\text{ A}$ (Note 2)		0.7	1.2	V
t_{rr}	Diode Reverse Recovery Time	$I_F = 9\text{ A}$		20		nS
Q_{rr}	Diode Reverse Recovery Charge	$d_I/d_t = 100\text{ A}/\mu\text{s}$		14		nC

Notes:

- $R_{\theta JA}$ is determined with the device mounted on a 1 in² 2 oz. copper pad on a 1.5 x 1.5 in. board of FR-4 material. The thermal resistance from the junction to the circuit board side of the solder ball, $R_{\theta JB}$, is defined for reference. For $R_{\theta JC}$, the thermal reference point for the case is defined as the top surface of the copper chip carrier. $R_{\theta JC}$ and $R_{\theta JB}$ are guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.



- a) 67 $^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper, 1.5" x 1.5" x 0.062" thick PCB

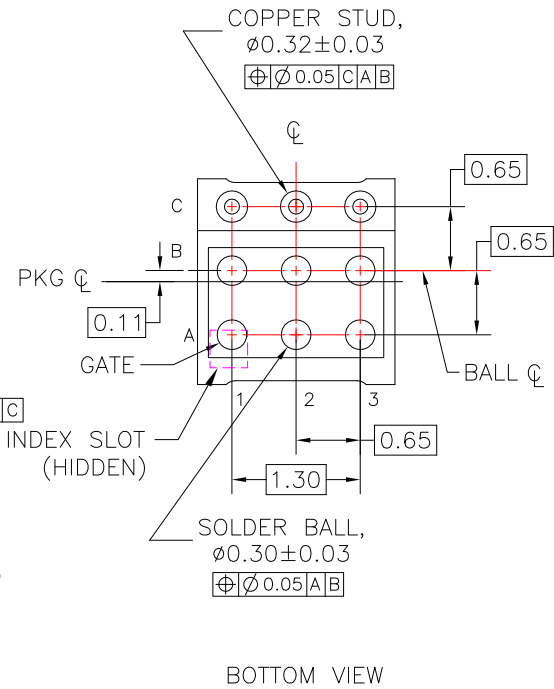
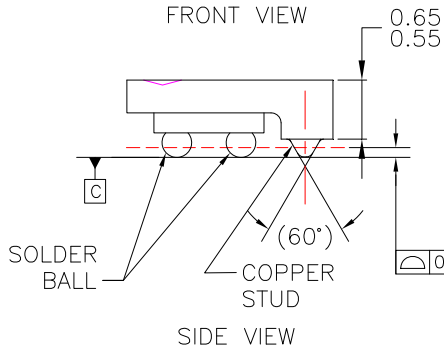
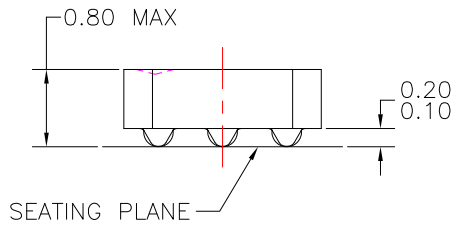
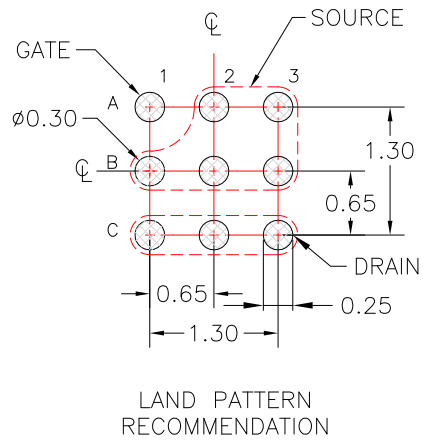
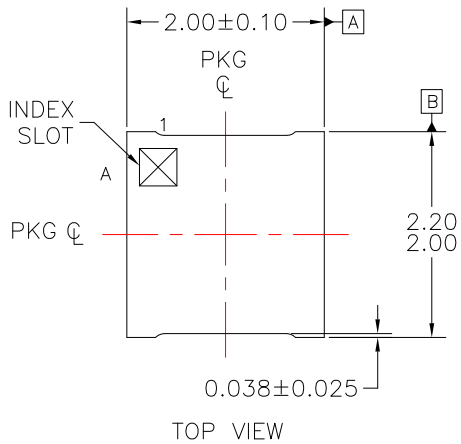


- b) 155 $^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

Dimensional Outline and Pad Layout



NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PKG IS NOT PRESENTLY REGISTERED WITH ANY STANDARDS COMMITTEE.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-1994.
- D) LAND PATTERN NAME: BGA9C65P3X3_200X200X80
- E) TERMINAL CONFIGURATION TABLE.

POSITION	DESIGNATION	TYPE
C1,C2,C3	DRAIN	COPPER STUD
A1	GATE	SOLDER BALL
A2,A3,B1,B2,B3	SOURCE	SOLDER BALL

F) DRAWING FILENAME: MKT-BGA06Brev6

Typical Characteristics

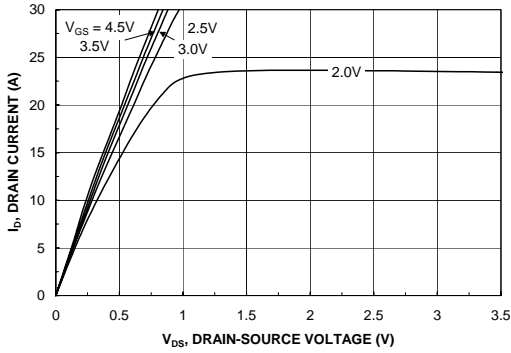


Figure 1. On-Region Characteristics.

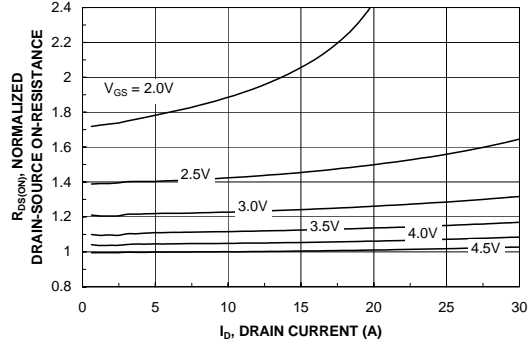


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

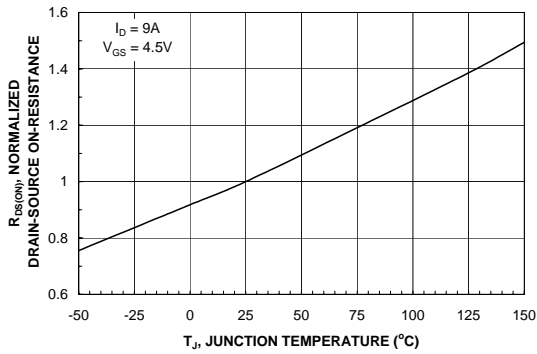


Figure 3. On-Resistance Variation with Temperature.

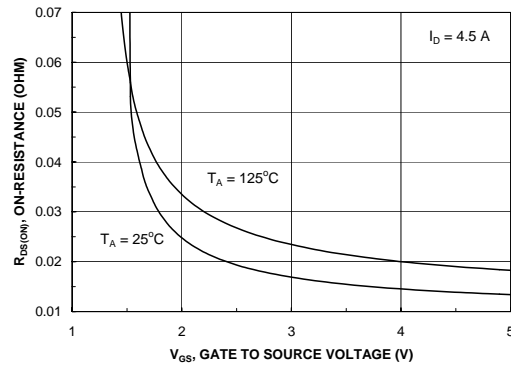


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

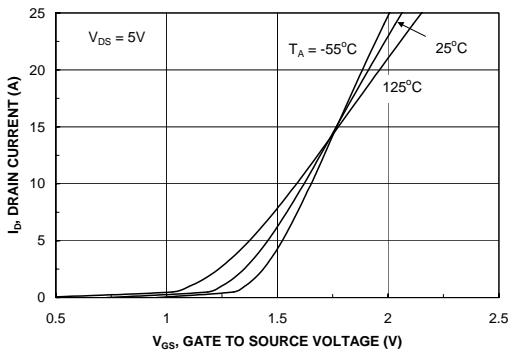


Figure 5. Transfer Characteristics.

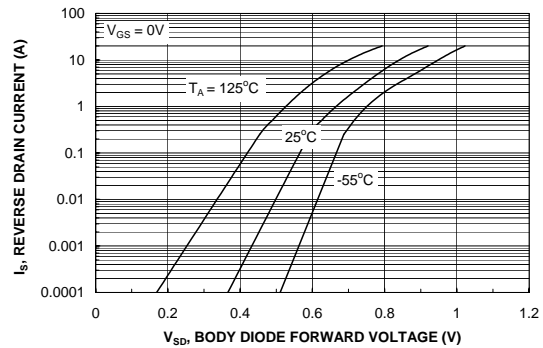


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

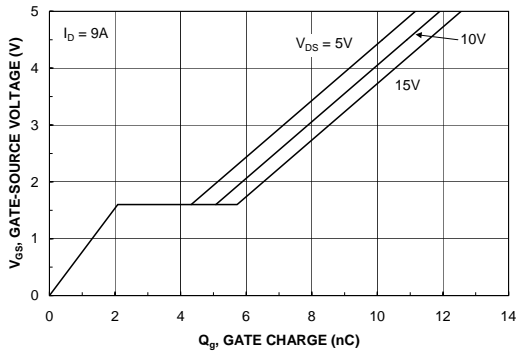


Figure 7. Gate Charge Characteristics.

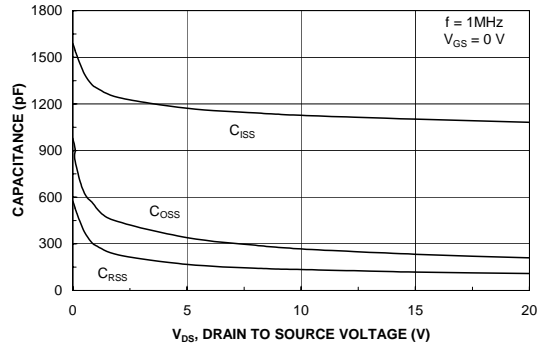


Figure 8. Capacitance Characteristics.

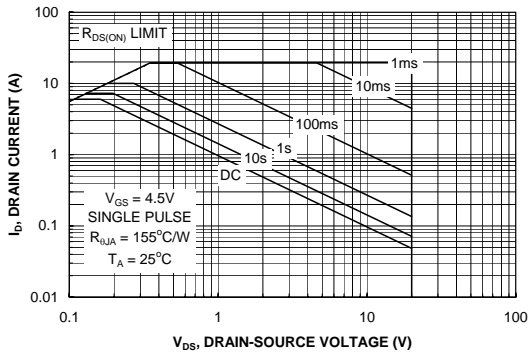


Figure 9. Maximum Safe Operating Area.

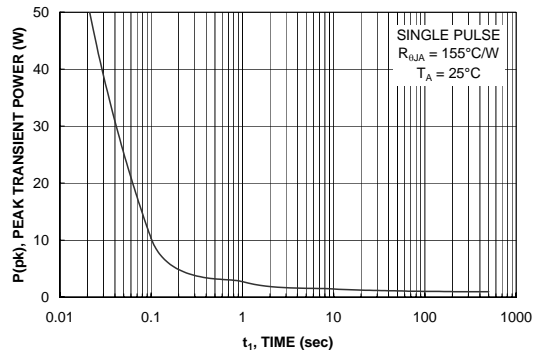


Figure 10. Single Pulse Maximum Power Dissipation.

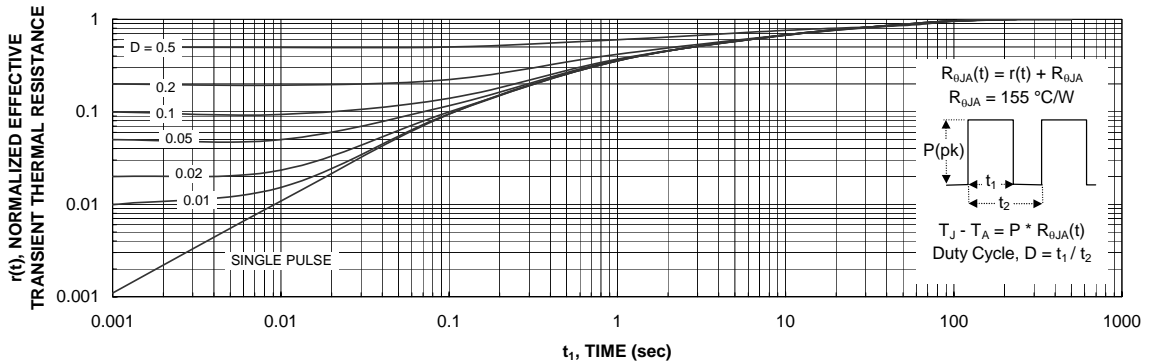







Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.



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